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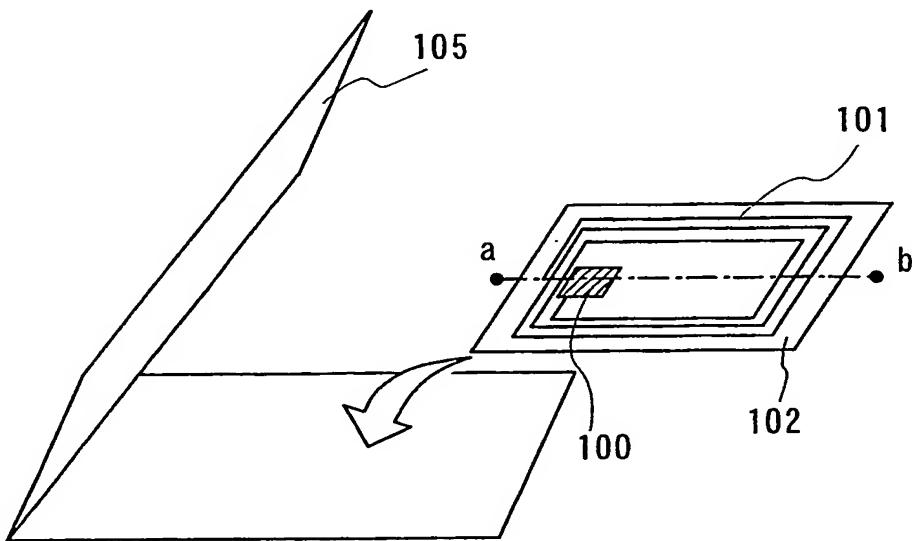
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(54) Title: FILM-LIKE ARTICLE AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: Since the chip formed from a silicon wafer is thick, the chip is protruded from the surface or the chip is so large that it can be seen through the eyes, which affects the design of a business card or the like. Hence, it is an object of the present invention to provide a new integrated circuit which has a structure by which the design is not affected. In view of the above problems, it is a feature of the invention to equip a film-like article with a thin film integrated circuit. It is another feature of the invention that the IDI[®] chip has a semiconductor film of 0.2 mm or less, as an active region. Therefore, the IDI[®] chip can be made thinner as compared with a chip formed from a silicon wafer. In addition, such an integrated circuit can have light transmitting characteristic unlike a chip formed from a silicon wafer.

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